

Dafine Ravelosona

List of Publications by Year in descending order

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168
papers

7,062
citations

76326

40
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62596

80
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171
all docs

171
docs citations

171
times ranked

5076
citing authors

#	ARTICLE	IF	CITATIONS
1	Current-induced magnetization reversal in nanopillars with perpendicular anisotropy. <i>Nature Materials</i> , 2006, 5, 210-215.	27.5	1,148
2	Compact Modeling of Perpendicular-Anisotropy CoFeB/MgO Magnetic Tunnel Junctions. <i>IEEE Transactions on Electron Devices</i> , 2012, 59, 819-826.	3.0	330
3	Tailoring magnetism by light-ion irradiation. <i>Journal Physics D: Applied Physics</i> , 2004, 37, R179-R196.	2.8	261
4	Strain-controlled magnetic domain wall propagation in hybrid piezoelectric/ferromagnetic structures. <i>Nature Communications</i> , 2013, 4, 1378.	12.8	237
5	Non-adiabatic spin-torques in narrow magnetic domain walls. <i>Nature Physics</i> , 2010, 6, 17-21.	16.7	194
6	Failure and reliability analysis of STT-MRAM. <i>Microelectronics Reliability</i> , 2012, 52, 1848-1852.	1.7	192
7	The nature of domain walls in ultrathin ferromagnets revealed by scanning nanomagnetometry. <i>Nature Communications</i> , 2015, 6, 6733.	12.8	183
8	Reducing the critical current for spin-transfer switching of perpendicularly magnetized nanomagnets. <i>Applied Physics Letters</i> , 2009, 94, .	3.3	171
9	Nanoscale imaging and control of domain-wall hopping with a nitrogen-vacancy center microscope. <i>Science</i> , 2014, 344, 1366-1369.	12.6	158
10	Chemical order induced by ion irradiation in FePt (001) films. <i>Applied Physics Letters</i> , 2000, 76, 236-238.	3.3	151
11	Nanometer Scale Observation of High Efficiency Thermally Assisted Current-Driven Domain Wall Depinning. <i>Physical Review Letters</i> , 2005, 95, 117203.	7.8	149
12	Reconfigurable Codesign of STT-MRAM Under Process Variations in Deeply Scaled Technology. <i>IEEE Transactions on Electron Devices</i> , 2015, 62, 1769-1777.	3.0	135
13	Ordering Intermetallic Alloys by Ion Irradiation: A Way to Tailor Magnetic Media. <i>Physical Review Letters</i> , 2003, 91, 077203.	7.8	131
14	Damping of CoFe ₈₀ B ₂₀ ultrathin films with perpendicular magnetic anisotropy. <i>Applied Physics Letters</i> , 2013, 102, .	3.3	126
15	Ferromagnetic resonance linewidth in ultrathin films with perpendicular magnetic anisotropy. <i>Physical Review B</i> , 2009, 80, .	3.2	124
16	Domain Wall Creep in Magnetic Wires. <i>Physical Review Letters</i> , 2004, 92, 107202.	7.8	121
17	Perpendicular-magnetic-anisotropy CoFeB racetrack memory. <i>Journal of Applied Physics</i> , 2012, 111, .	2.5	111
18	Threshold currents to move domain walls in films with perpendicular anisotropy. <i>Applied Physics Letters</i> , 2007, 90, 072508.	3.3	101

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19	Low depinning fields in Ta-CoFeB-MgO ultrathin films with perpendicular magnetic anisotropy. Applied Physics Letters, 2013, 103, 182401.	3.3	90
20	Synchronous Non-Volatile Logic Gate Design Based on Resistive Switching Memories. IEEE Transactions on Circuits and Systems I: Regular Papers, 2014, 61, 443-454.	5.4	90
21	Spintronics. ACM Journal on Emerging Technologies in Computing Systems, 2015, 12, 1-42.	2.3	83
22	Helium Ions Put Magnetic Skyrmions on the Track. Nano Letters, 2021, 21, 2989-2996.	9.1	79
23	Electrical Modeling of Stochastic Spin Transfer Torque Writing in Magnetic Tunnel Junctions for Memory and Logic Applications. IEEE Transactions on Magnetics, 2013, 49, 4375-4378.	2.1	74
24	Domain-wall scattering in epitaxial FePd ordered alloy films with perpendicular magnetic anisotropy. Physical Review B, 1999, 59, 4322-4326.	3.2	72
25	Failure Analysis in Magnetic Tunnel Junction Nanopillar with Interfacial Perpendicular Magnetic Anisotropy. Materials, 2016, 9, 41.	2.9	72
26	Self-Enabled "Error-Free" Switching Circuit for Spin Transfer Torque MRAM and Logic. IEEE Transactions on Magnetics, 2012, 48, 2403-2406.	2.1	71
27	Domain Wall Creation in Nanostructures Driven by a Spin-Polarized Current. Physical Review Letters, 2006, 96, 186604.	7.8	67
28	Magnetization reversal assisted by the inverse piezoelectric effect in Co-Fe-B ferroelectric multilayers. Physical Review B, 2011, 84, .	3.2	67
29	Thermally Activated Depinning of a Narrow Domain Wall from a Single Defect. Physical Review Letters, 2006, 96, 147204.	7.8	60
30	A radiation hardened hybrid spintronic/CMOS nonvolatile unit using magnetic tunnel junctions. Journal Physics D: Applied Physics, 2014, 47, 405003.	2.8	60
31	Yield and Reliability Improvement Techniques for Emerging Nonvolatile STT-MRAM. IEEE Journal on Emerging and Selected Topics in Circuits and Systems, 2015, 5, 28-39.	3.6	57
32	Enhancement of the Dzyaloshinskii-Moriya interaction and domain wall velocity through interface intermixing in Ta/CoFeB/MgO. Physical Review B, 2019, 99, .	3.2	56
33	Domain wall memory: Physics, materials, and devices. Physics Reports, 2022, 958, 1-35.	25.6	56
34	Chemical order induced by He+ ion irradiation in FePt (001) films. Journal of Applied Physics, 2000, 87, 5771-5773.	2.5	54
35	Domain Wall Shift Register-Based Reconfigurable Logic. IEEE Transactions on Magnetics, 2011, 47, 2966-2969.	2.1	54
36	Influence of geometry on domain wall propagation in a mesoscopic wire. IEEE Transactions on Magnetics, 2001, 37, 2104-2107.	2.1	53

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37	Variation-Tolerant and Disturbance-Free Sensing Circuit for Deep Nanometer STT-MRAM. IEEE Nanotechnology Magazine, 2014, 13, 1088-1092.	2.0	52
38	Compact Modeling of Perpendicular-Magnetic-Anisotropy Double-Barrier Magnetic Tunnel Junction With Enhanced Thermal Stability Recording Structure. IEEE Transactions on Electron Devices, 2019, 66, 2431-2436.	3.0	51
39	High reliability sensing circuit for deep submicron spin transfer torque magnetic random access memory. Electronics Letters, 2013, 49, 1283-1285.	1.0	49
40	A low-cost built-in error correction circuit design for STT-MRAM reliability improvement. Microelectronics Reliability, 2013, 53, 1224-1229.	1.7	43
41	Controlling magnetic domain wall motion in the creep regime in He ⁺ -irradiated CoFeB/MgO films with perpendicular anisotropy. Applied Physics Letters, 2015, 107, .	3.3	41
42	Magnetic logic using nanowires with perpendicular anisotropy. Nanotechnology, 2009, 20, 215401.	2.6	40
43	Role of pinning in current driven domain wall motion in wires with perpendicular anisotropy. Applied Physics Letters, 2008, 93, 172513.	3.3	39
44	Irradiation-induced tailoring of the magnetism of CoFeB/MgO ultrathin films. Journal of Applied Physics, 2013, 113, .	2.5	39
45	Universal domain wall dynamics under electric field in Ta/CoFeB/MgO devices with perpendicular anisotropy. Nature Communications, 2016, 7, 13532.	12.8	37
46	Beam-induced magnetic property modifications: Basics, nanostructure fabrication and potential applications. Nuclear Instruments & Methods in Physics Research B, 2001, 175-177, 375-381.	1.4	34
47	Enhancing domain wall velocity through interface intermixing in W-CoFeB-MgO films with perpendicular anisotropy. Applied Physics Letters, 2019, 115, .	3.3	34
48	Compact modelling of ferroelectric tunnel memristor and its use for neuromorphic simulation. Applied Physics Letters, 2014, 104, 053505.	3.3	32
49	The influence of the Pt buffer layer on the perpendicular magnetic anisotropy in epitaxial FePd(001) ordered alloys grown by sputtering. Journal of Applied Physics, 1997, 81, 5050-5052.	2.5	31
50	Growth of [YBa ₂ Cu ₃ O _{7-δ}]/[PrBa ₂ Cu _{3-x} GaxO _{7-δ}]NSuperlattices by Pulsed Laser Deposition. Japanese Journal of Applied Physics, 1993, 32, L1134-L1136.	1.5	30
51	MFM imaging of FePd stripe domains. Evolution with Pt buffer layer thickness. Journal of Magnetism and Magnetic Materials, 1999, 196-197, 23-25.	2.3	30
52	A compact model of domain wall propagation for logic and memory design. Journal of Applied Physics, 2011, 109, .	2.5	29
53	Measuring the Magnetic Moment Density in Patterned Ultrathin Ferromagnets with Submicrometer Resolution. Physical Review Applied, 2015, 4, .	3.8	29
54	Telegraph noise due to domain wall motion driven by spin current in perpendicular magnetized nanopillars. Applied Physics Letters, 2009, 94, .	3.3	28

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55	Effective field analysis using the full angular spin-orbit torque magnetometry dependence. Physical Review B, 2017, 95, .	3.2	27
56	Direct Observation of Domain-Wall Surface Tension by Deflating or Inflating a Magnetic Bubble. Physical Review Applied, 2018, 9, .	3.8	27
57	Chemical ordering at low temperatures in FePd films. Journal of Applied Physics, 2002, 91, 8082.	2.5	25
58	State diagram of nanopillar spin valves with perpendicular magnetic anisotropy. Physical Review B, 2012, 86, .	3.2	25
59	Tailoring magnetism in CoNi films with perpendicular anisotropy by ion irradiation. Journal of Applied Physics, 2008, 103, 07B529.	2.5	24
60	Design of MRAM based logic circuits and its applications. , 2011, , .		24
61	A physics-based compact model of ferroelectric tunnel junction for memory and logic design. Journal Physics D: Applied Physics, 2014, 47, 045001.	2.8	24
62	Enhancing domain wall motion in magnetic wires by ion irradiation. Applied Physics Letters, 2005, 86, 022503.	3.3	23
63	Influence of ion irradiation on switching field and switching field distribution in arrays of Co/Pd-based bit pattern media. Applied Physics Letters, 2011, 98, 172506.	3.3	22
64	Measurement of magnetization using domain compressibility in CoFeB films with perpendicular anisotropy. Applied Physics Letters, 2014, 104, .	3.3	22
65	Separated Precharge Sensing Amplifier for Deep Submicrometer MTJ/CMOS Hybrid Logic Circuits. IEEE Transactions on Magnetics, 2014, 50, 1-5.	2.1	22
66	Domain-Wall Motion Driven by Laplace Pressure in $\text{Co}/\text{Fe}/\text{MgO}$ Nanodots with Perpendicular Anisotropy. Physical Review Applied, 2018, 9, .	3.3	22
67	Nonvolatile Boolean Logic Block Based on Ferroelectric Tunnel Memristor. IEEE Transactions on Magnetics, 2014, 50, 1-4.	2.1	20
68	Ferromagnetic resonance study of Co/Pd/Co/Ni multilayers with perpendicular anisotropy irradiated with helium ions. Journal of Applied Physics, 2011, 109, .	2.5	19
69	Reversible Charge-Transfer Doping in Graphene due to Reaction with Polymer Residues. Journal of Physical Chemistry C, 2014, 118, 13890-13897.	3.1	19
70	Spin-orbit torque driven multi-level switching in He ⁺ irradiated CoFeB/MgO Hall bars with perpendicular anisotropy. Applied Physics Letters, 2020, 116, .	3.3	19
71	Reduced spin torque nano-oscillator linewidth using He + irradiation. Applied Physics Letters, 2020, 116, 072403.	3.3	19
72	Homoepitaxial growth of low roughness SrTiO ₃ by pulsed laser deposition: application to YBa ₂ Cu ₃ O _{7-x} -based thin films and superlattices. Journal of Crystal Growth, 1994, 141, 141-149.	1.5	18

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73	Perspectives of Racetrack Memory for Large-Capacity On-Chip Memory: From Device to System. IEEE Transactions on Circuits and Systems I: Regular Papers, 2016, 63, 629-638.	5.4	18
74	Electric field controlled domain wall dynamics and magnetic easy axis switching in liquid gated CoFeB/MgO films. Journal of Applied Physics, 2017, 122, .	2.5	18
75	Dynamics of magnetization reversal in a mesoscopic wire. Journal of Magnetism and Magnetic Materials, 2002, 249, 170-174.	2.3	17
76	An overview of spin-based integrated circuits. , 2014, , .		17
77	Ring-shaped Racetrack memory based on spin orbit torque driven chiral domain wall motions. Scientific Reports, 2016, 6, 35062.	3.3	17
78	Multi-level cell Spin Transfer Torque MRAM based on stochastic switching. , 2013, , .		16
79	Spintronics for low-power computing. , 2014, , .		16
80	Magnetic domain-wall racetrack memory for high density and fast data storage. , 2012, , .		15
81	Interface width evaluation in thin layered CoFeB/MgO multilayers including Ru or Ta buffer layer by X-ray reflectivity. Thin Solid Films, 2013, 533, 79-82.	1.8	15
82	Current induced perpendicular-magnetic-anisotropy racetrack memory with magnetic field assistance. Applied Physics Letters, 2014, 104, .	3.3	15
83	DFSTT-MRAM: Dual Functional STT-MRAM Cell Structure for Reliability Enhancement and 3-D MLC Functionality. IEEE Transactions on Magnetics, 2014, 50, 1-7.	2.1	14
84	Design and analysis of crossbar architecture based on complementary resistive switching non-volatile memory cells. Journal of Parallel and Distributed Computing, 2014, 74, 2484-2496.	4.1	14
85	A Multilevel Cell for STT-MRAM Realized by Capping Layer Adjustment. IEEE Transactions on Magnetics, 2015, 51, 1-4.	2.1	14
86	Demonstration of Multi-State Memory Device Combining Resistive and Magnetic Switching Behaviors. IEEE Electron Device Letters, 2018, 39, 684-687.	3.9	14
87	Magnetic properties of irradiated highly anisotropic materials. IEEE Transactions on Magnetics, 2001, 37, 1643-1645.	2.1	13
88	Detection of domain wall propagation in a mesoscopic wire. Journal of Magnetism and Magnetic Materials, 2002, 240, 30-33.	2.3	13
89	Coercivity enhancement in FePt nanowires due to the suppression of available paths for domain wall propagation. Physical Review B, 2011, 84, .	3.2	13
90	Perpendicular magnetic anisotropy in Ta/CoFeB/MgO systems synthesized on treated SiN/SiO2 substrates for magnetic memories. Thin Solid Films, 2013, 533, 75-78.	1.8	13

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91	Heterogeneous Memristive Devices Enabled by Magnetic Tunnel Junction Nanopillars Surrounded by Resistive Silicon Switches. <i>Advanced Electronic Materials</i> , 2018, 4, 1700461.	5.1	13
92	Energy-Efficient Domain-Wall Motion Governed by the Interplay of Helicity-Dependent Optical Effect and Spin-Orbit Torque. <i>Physical Review Applied</i> , 2019, 11, .	3.8	13
93	Spin-orbit torques for current parallel and perpendicular to a domain wall. <i>Applied Physics Letters</i> , 2015, 107, .	3.3	12
94	Thermally activated domain wall motion in [Co/Ni](111) superlattices with perpendicular magnetic anisotropy. <i>Applied Physics Letters</i> , 2015, 106, .	3.3	12
95	Complementary Spintronic Logic With Spin Hall Effect-Driven Magnetic Tunnel Junction. <i>IEEE Transactions on Magnetics</i> , 2015, 51, 1-4.	2.1	12
96	High Performance SoC Design Using Magnetic Logic and Memory. <i>International Federation for Information Processing</i> , 2012, , 10-33.	0.4	12
97	Current induced domain wall states in CPP nanopillars with perpendicular anisotropy. <i>Journal Physics D: Applied Physics</i> , 2007, 40, 1253-1256.	2.8	11
98	Write operation study of Co/BTO/LSMO ferroelectric tunnel junction. <i>Journal of Applied Physics</i> , 2013, 114, 044108.	2.5	11
99	Ionic-liquid gating of perpendicularly magnetised CoFeB/MgO thin films. <i>Journal of Applied Physics</i> , 2016, 120, .	2.5	11
100	Extrinsic pinning of magnetic domain walls in CoFeB-MgO nanowires with perpendicular anisotropy. <i>AIP Advances</i> , 2018, 8, .	1.3	11
101	Wire edge dependent magnetic domain wall creep. <i>Physical Review B</i> , 2018, 98, .	3.2	11
102	Tailoring interfacial effect in multilayers with Dzyaloshinskiiâ€Moriya interaction by helium ion irradiation. <i>Scientific Reports</i> , 2021, 11, 23626.	3.3	11
103	Propagation of a magnetic domain wall in the presence of AFM fabricated defects. <i>IEEE Transactions on Magnetics</i> , 2001, 37, 2331-2333.	2.1	10
104	Control of the magnetic domain wall propagation in Pt/Co/Pt ultra thin films using direct mechanical AFM lithography. <i>Journal of Magnetism and Magnetic Materials</i> , 2002, 240, 53-56.	2.3	10
105	Variation-Tolerant High-Reliability Sensing Scheme for Deep Submicrometer STT-MRAM. <i>IEEE Transactions on Magnetics</i> , 2014, 50, 1-4.	2.1	10
106	From Device to System: Cross-layer Design Exploration of Racetrack Memory. , 2015, , .		10
107	Peristaltic perpendicular-magnetic-anisotropy racetrack memory based on chiral domain wall motions. <i>Journal Physics D: Applied Physics</i> , 2015, 48, 105001.	2.8	10
108	Magnetoâ€ionics in Annealed W/CoFeB/HfO ₂ Thin Films. <i>Advanced Materials Interfaces</i> , 2022, 9, .	3.7	10

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109	Stochastic domain-wall depinning under current in FePt spin valves and single layers. Physical Review B, 2011, 84, .	3.2	9
110	Domain wall motion in nanopillar spin-valves with perpendicular anisotropy driven by spin-transfer torques. Physical Review B, 2012, 86, .	3.2	9
111	High Density Spin-Transfer Torque (STT)-MRAM Based on Cross-Point Architecture. , 2012, , .		9
112	Magneto-resistive sensors based on the elasticity of domain walls. Nanotechnology, 2018, 29, 365502.	2.6	9
113	Critical thickness and stress relaxation in YBaCuO (123) strained epitaxial layers and YBaCuO based strained superlattices. Zeitschrift für Physik B-Condensed Matter, 1996, 100, 185-190.	1.1	8
114	Vortex-lattice activation energy deduced from irreversibility lines for $(\text{PrBa}_2\text{Cu}_3\text{xGaxO}_7)\text{M}/(\text{YBa}_2\text{Cu}_3\text{O}_7)\text{N}$ superlattices. Physical Review B, 2000, 61, 7044-7048.	3.2	8
115	Design and analysis of Racetrack memory based on magnetic domain wall motion in nanowires. , 2014, , .		8
116	Multiple Magnetoionic Regimes in $\text{Ta/Co}_{20}/\text{Fe}_{20}/\text{B}_{20}/\text{O}$ Multilayers. Physical Review Applied, 2021, 15, .	3.8	8
117	Irradiation-induced magnetic patterning in magnetic multilayers. Materials Science and Engineering C, 2001, 15, 53-58.	7.3	7
118	Interplay between collective pinning and artificial defects on domain wall propagation in Co/Pt multilayers. Journal Physics D: Applied Physics, 2010, 43, 305002.	2.8	7
119	Perpendicular magnetic anisotropy in piezoelectric- and dielectric-ferromagnetic heterostructures based on Co/Pt multilayers. Thin Solid Films, 2013, 533, 70-74.	1.8	7
120	Readability challenges in deeply scaled STT-MRAM. , 2014, , .		7
121	Dynamic Reference Sensing Scheme for Deeply Scaled STT-MRAM. , 2015, , .		7
122	Statistical study of domain-wall depinning induced by magnetic field and current in an epitaxial Co/Ni-based spin-valve wire. Physical Review B, 2018, 98, .	3.2	7
123	In situ monitoring of electric field effect on domain wall motion in Co ultrathin films in direct contact with an electrolyte. Applied Physics Letters, 2019, 115, .	3.3	7
124	Low Spin Polarization in Heavy-Metal-Ferromagnet Structures Detected Through Domain-Wall Motion by Synchronized Magnetic Field and Current. Physical Review Applied, 2019, 11, .	3.8	7
125	Domain-wall motion induced by spin transfer torque delivered by helicity-dependent femtosecond laser. Physical Review B, 2019, 99, .	3.2	7
126	Magnetic domain wall curvature induced by wire edge pinning. Applied Physics Letters, 2020, 117, .	3.3	7

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127	Growth mode and matrix effects on the magneto-optical activity of ultrathin films. Applied Physics Letters, 2002, 81, 1603-1605.	3.3	6
128	Effects of patterning on perpendicular exchange bias probed by extraordinary Hall effect. Journal of Applied Physics, 2004, 95, 6726-6728.	2.5	6
129	Spin-electronics based logic fabrics. , 2013, , .		6
130	Design and analysis of racetrack memory based on magnetic domain wall motion in nanowires. , 2014, , .		6
131	Perspectives of racetrack memory based on current-induced domain wall motion: From device to system. , 2015, , .		6
132	Effect of spin transfer torque on domain wall motion regimes in [Co/Ni] superlattice wires. Physical Review B, 2017, 95, .	3.2	6
133	Suppression of all-optical switching in He ⁺ -irradiated Co/Pt multilayers: influence of the domain-wall energy. Journal Physics D: Applied Physics, 2018, 51, 215004.	2.8	6
134	Ion irradiation and implantation modifications of magneto-ionically induced exchange bias in Gd/NiCoO. Journal of Magnetism and Magnetic Materials, 2021, 540, 168479.	2.3	6
135	Study of (YBa ₂ Cu ₃ O _{7-x}) _{1-x} M/(PrBa ₂ Cu ₃ O _{7-x}) _{1-x} N superlattices grown by pulsed-laser deposition: a comparison between a - and c-axis oriented structures. Applied Surface Science, 1994, 75, 252-258.	6.1	5
136	Current-induced magnetization reversal in nanopillars with perpendicular anisotropy. , 2006, , .		5
137	SPINTRONIC MEMORY-BASED RECONFIGURABLE COMPUTING. Spin, 2013, 03, 1340010.	1.3	5
138	A novel SEU-tolerant MRAM latch circuit based on C-element. , 2014, , .		5
139	Spintronics for low-power computing. , 2014, , .		5
140	Implementation of magnetic field assistance to current-induced perpendicular-magnetic-anisotropy racetrack memory. Journal of Applied Physics, 2014, 115, 17D509.	2.5	5
141	Recent developments in the manipulation of magnetic domain walls in CoFeB/MgO wires for applications to high-density nonvolatile memories. , 2015, , 333-378.		5
142	Critical thickness of YBaCuO (123) strained thin films and superlattices grown by pulsed laser deposition. Applied Surface Science, 1996, 96-98, 703-707.	6.1	4
143	Growth defects and interface roughness in YBa ₂ Cu ₃ O ₇ /SrTiO ₃ superlattices grown by pulsed laser ablation. Journal of Alloys and Compounds, 1997, 251, 185-192.	5.5	4
144	Buffer layer morphology effects on the ordering of epitaxial FePd(001) thin films. Acta Materialia, 1998, 46, 2299-2303.	7.9	4

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145	Study of domain wall propagation in nanostructured CoPt multilayers by using antisymmetric magnetoresistance. Journal of Physics: Conference Series, 2010, 200, 042021.	0.4	4
146	Asymmetric domain wall depinning under current in spin valves with perpendicular anisotropy. Applied Physics Letters, 2011, 98, 232512.	3.3	4
147	Crossbar architecture based on 2R complementary resistive switching memory cell. , 2012, , .		4
148	Engineering Domain-Wall Motion in $\langle \text{Co} \rangle \langle \text{Fe} \rangle \langle \text{B} \rangle \langle \text{Mg} \rangle \langle \text{O} \rangle$ Ultrathin Films with Perpendicular Anisotropy Using Patterned Substrates with Subnanometer Step Modulation. Physical Review Applied, 2018, 10, .	3.8	4
149	Buffer layer morphology effects on the ordering of epitaxial FePd(001) thin films. Acta Materialia, 1998, 46, 2299-2303.	7.9	4
150	Magnetisation measurements and irreversibility lines in (PrBa ₂ Cu ₃ â ^x GaxO ₇)M/(YBa ₂ Cu ₃ O ₇)N superlattices. Physica C: Superconductivity and Its Applications, 1994, 235-240, 2721-2722.	1.2	3
151	Analytical study of complementary memristive synchronous logic gates. , 2013, , .		3
152	Synchronous full-adder based on complementary resistive switching memory cells. , 2013, , .		3
153	Tuning the magnetodynamic properties of all-perpendicular spin valves using He ⁺ irradiation. AIP Advances, 2018, 8, 065309.	1.3	3
154	Dynamics of Domain Wall Motion in Wires with Perpendicular Anisotropy. , 2009, , 185-217.		3
155	Structural and electrical properties of PrBa ₂ Cu ₃ â ^x GaxO ₇ (x = 0.2) thin films and Alloys and Compounds, 1997, 251, 209-212.	5.5	2
156	Current-driven narrow domain wall depinning in perpendicular spin valves. IEEE Transactions on Magnetics, 2005, 41, 2618-2620.	2.1	2
157	A dynamic reference scheme to improve the sensing reliability of magnetic random access memory. , 2014, , .		2
158	Controlling magnetism by interface engineering. , 2020, , 361-379.		2
159	Domain wall creep in a 2D magnetic wire in the presence of antiferromagnetic coupling. Journal Physics D: Applied Physics, 2013, 46, 235001.	2.8	1
160	Emerging hybrid logic circuits based on non-volatile magnetic memories. , 2013, , .		1
161	Voltage control of magnetism in ferromagnetic structures. Proceedings of SPIE, 2012, , .	0.8	0
162	Compact modelling for Co/BTO/LSMO Ferroelectric Tunnel Junction. , 2013, , .		0

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163	Domain wall dynamics under electric field in Ta/Co ₄₀ /Fe ₄₀ /B ₂₀ /MgO devices with perpendicular anisotropy. , 2015, , .		0
164	Complementary spintronic logic with spin hall effect driven magnetic tunnel junction. , 2015, , .		0
165	Non-volatile memories: Materials, nanostructures and integration approaches. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 235-236.	1.8	0
166	ECRIS/EBIS Based Low-Energy Ion Implantation Technologies. , 2018, , .		0
167	Croissance de PrBa ₂ Cu ₃ -xGaxO ₇ en ablation laser pulsée : application aux superconducteurs (YBa ₂ Cu ₃ O ₇) _M /(PrBa ₂ Cu ₃ -xGaxO ₇) _N . Journal De Physique III, 1994, 4, 2173-2182.	0.3	0
168	Critical thickness of YBaCuO (123) strained thin films and superlattices grown by pulsed laser deposition. , 1996, , 703-707.		0